SEMICONDUCTOR DEVICE PACKAGE AND METHOD OF MANUFACTURING THEREOF

ABSTRACT

A semiconductor device package includes a semiconductor device having connection pads formed thereon, with the connection pads being formed on first and second surfaces of the semiconductor device with edges of the semiconductor device extending therebetween. A first passivation layer is applied on the semiconductor device and a base dielectric laminate is affixed to the first surface of the semiconductor device that has a thickness greater than that of the first passivation layer. A second passivation layer having a thickness greater than that of the first passivation layer is applied over the first passivation layer and the semiconductor device to cover the second surface and the edges of the semiconductor device, and metal interconnects are coupled to the connection pads, with the metal interconnects extending through vias formed through the first and second passivation layers and the base dielectric laminate sheet to form a connection with the connection pads.

Figure 1